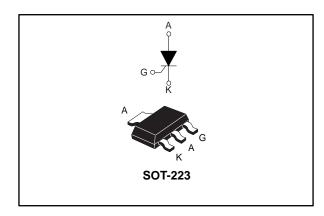
P0102DN



Sensitive 0.8 A SCR thyristor

Datasheet - production data



Features

- I_{T(RMS)} 0.8 A
- 125 °C max T_i
- Low 0.2 mA gate current
- 400 V V_{DRM}/V_{RRM}
- ECOPACK®2 compliant component

Applications

- Proximity sensors
- Gate driver for large Thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Solid state relay pilot circuit
- Standby mode power supplies
- Residual current detector

Description

Thanks to highly sensitive triggering levels, the 0.8 A P0102DN SCR thyristor is suitable for all applications where available gate current is limited. This device offers a high blocking voltage of 400 V, ideal for applications like interrupters circuits in 110 V mains regions.

The surface mount SOT-223 package allows compact, SMD based designs for automated manufacturing.

Table 1: Device summary

Symbol	Value	Unit
I _{T(RMS)}	0.8	А
V _{DRM} /V _{RRM}	400	V
I _{GT}	0.2	mA
T _j max.	125	°C

Characteristics P0102DN

1 Characteristics

Table 2: Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter	Value	Unit		
I _{T(RMS)}	RMS on-state current (180 ° conduction	T _{amb} = 70 °C	0.8	Λ	
I _{T(AV)}	Average on-state current (180 ° conduc	ction angle)	Tamb = 70 C	0.5	Α
	(T : it I of oo		$t_p = 8.3 \text{ ms}$	8	Α
I _{TSM}			t _p = 10 ms	7	A
l ² t	I ² t value for fusing	$t_p = 10 \text{ ms}$	0.24	A ² s	
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $I_T \le 100 \text{ ns}$ $f = 60 \text{ Hz}$		T _j = 125 °C	50	A/µs
V _{DRM} /V _{RRM}	Repetitive peak off-state voltage	T _j = 125 °C	400	V	
I _{GM}	Peak gate current $t_p = 20 \mu s$		T _j = 125 °C	1	Α
P _{G(AV)}	Average gate power dissipation	0.1	W		
T _{stg}	Storage junction temperature range			-40 to +150	°C
Tj	Operating junction temperature			-40 to +125	°C

Table 3: Electrical characteristics ($T_j = 25$ °C unless otherwise specified)

Symbol	Test conditions		Value	Unit	
lgт	V 40 V B 440 O		Max.	200	μΑ
V _G T	$V_D = 12 \text{ V}, R_L = 140 \Omega$		Max.	0.8	V
V_{GD}	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, R_{GK} = 1000 \Omega$	Min.	0.1	V	
V_{RG}	I _{RG} = 10 μA	Min.	8	V	
lΗ	$I_T = 50 \text{ mA}, R_{GK} = 1000 \Omega$	Max.	5	mA	
IL	$I_G = 1.2 \text{ x } I_{GT}, R_{GK} = 1000 \Omega$	Max.	6	mA	
dV/dt	$V_D = 67 \% V_{DRM}, R_{GK} = 1000 \Omega$ $T_j = 125 \ ^{\circ}C$		Min.	75	V/µs

Table 4: Static characteristics

Symbol	Test condition	Value	Unit		
V _{TM}	$I_{TM} = 1.6 \text{ A}, t_p = 380 \mu\text{s}$	T _j = 25 °C	Max.	1.95	V
V _{TO}	Threshold voltage	T _j = 125 °C	Max.	0.95	V
R_D	Dynamic resistance	T _j = 125 °C	Max.	600	mΩ
1 //	V V V D 4000.0	T _j = 25 °C	N.4	1	
IDRM/IRRM $V_D = V_{DRM}$; $V_R = V_{RRM}$, $R_{GK} = 1000 \Omega$		T _j = 125 °C	Max.	100	μA

Table 5: Thermal parameters

Symbol	Parameter	Value	Unit	
R _{th(j-t)}	Junction to tab (DC)		30	
R _{th(j-a)}	Junction to ambient (DC)	$S^{(1)} = 5 \text{ cm}^2$	60	°C/W

Notes:

47/

 $^{^{(1)}}S$ = copper surface under tab.

P0102DN Characteristics

1.1 Characteristics (curves)

P(W)

1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

0.1

Figure 2: Average and DC on-state current versus case temperature $I_{\mathsf{T}(\mathsf{AV})}(\mathsf{A})$ 1.0 0.9 0.8 0.7 0.6 0.5 0.4 0.3 0.2 0.1 T_{lead} (°C) 0.0 0 25 50 100 125

| T(AV)(A) | 1.2 | Device mounted on | FR4 with recommended | pad la yout for SOT-223 | 1.0 | Device mounted on | FR4 with recommended | pad la yout for SOT-223 | Device mounted on | FR4 with recommended | pad la yout for SOT-223 | Device mounted on | FR4 with recommended | pad la yout for SOT-223 | Device mounted on | FR4 with recommended | pad la yout for SOT-223 | Device mounted on | FR4 with recommended | pad la yout for SOT-223 | Device mounted on | PR4 with recommended | pad la yout for SOT-223 | Device mounted on | PR4 with recommended | pad la yout for SOT-223 | Device mounted on | PR4 with recommended | pad la yout for SOT-223 | Device mounted on | PR4 with recommended |

Figure 3: Average and DC on-state current versus

versus pulse duration

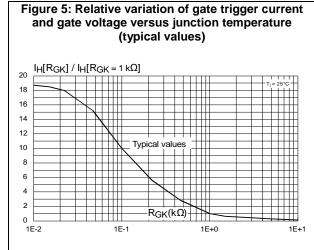
1.00 K=[Zth(j-a)/Rth(j-a)]

0.10 tp(s)

1.00 tp(s)

1.00 tp(s)

Figure 4: Relative variation of thermal impedance



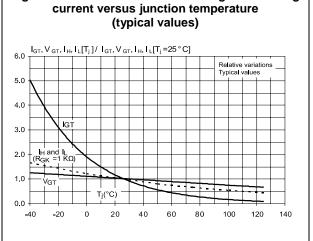


Figure 6: Relative variation of holding and latching

0.0

Characteristics P0102DN

Figure 7: Relative variation of static dV/dt immunity versus gate-cathode resistance (typical values)

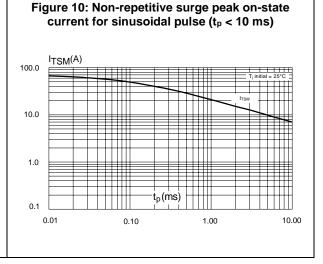
10.0

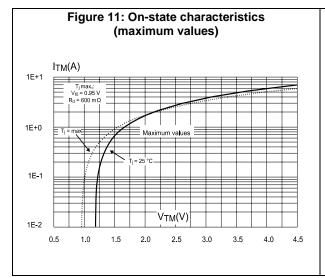
dV/dt[R_{GK}] / dV/dt[R_{GK} = 1kΩ]

1.0
Typical values

1.0
R_{GK}(kΩ)

0.1
0.2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 1.8 2.0





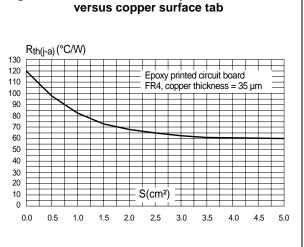


Figure 12: Thermal resistance junction to ambient

P0102DN Package information

2 **Package information**

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

- Lead-free package
- Halogen free molding resin
- Epoxy meets UL94, V0

SOT-223 package information 2.1

Figure 13: SOT-223 package outline

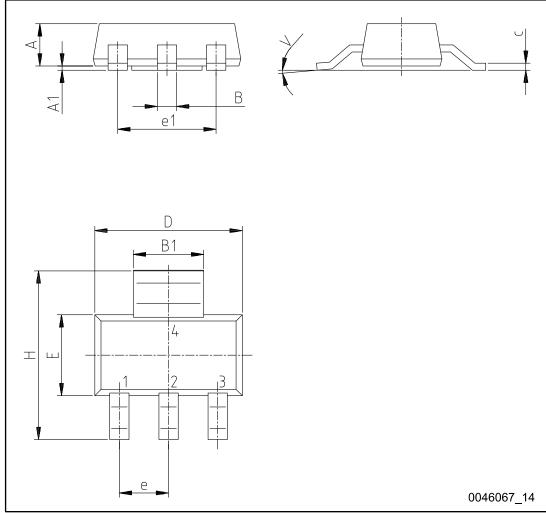


Table 6: SOT-223 package mechanical data

Dim.	Millimeters				Inches ⁽¹⁾	
Dilli.	Min.	Тур.	Max.	Min.	Тур.	Max.
А			1.8			0.0709
A1	0.02		0.1	0.0008		0.0039
В	0.6	0.7	0.85	0.0236	0.0276	0.0335
B1	2.9	3	3.15	0.1142	0.1181	0.1240
С	0.24	0.26	0.35	0.0094	0.0102	0.0138
D ⁽²⁾	6.3	6.5	6.7	0.2480	0.2559	0.2638
е		2.3			0.0906	
e1		4.6			0.1811	
E	3.3	3.5	3.7	0.1299	0.1378	0.1457
Н	6.7	7.0	7.3	0.2638	0.2756	0.2874
V			10°			10°

Notes:

3.3 6.4 1.5 4.6 0046067

Figure 14: SOT-223 recommended footprint (dimensions are in mm)

 $^{^{(1)}}$ Inches dimensions given only for reference

 $^{^{(2)}}$ Does not include mold flash or protusions. Mold flash or protusions must not exceed 0.15 mm (0.006 inches)

P0102DN Ordering information

3 Ordering information

Figure 15: Ordering information scheme

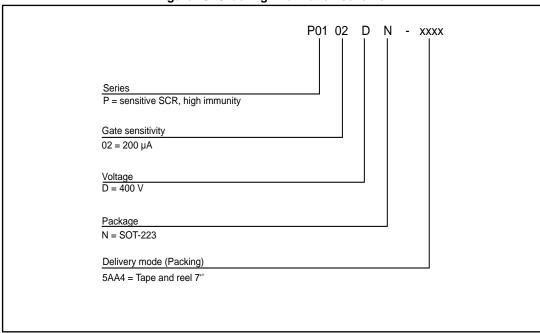


Table 7: Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
P0102DN 5AA4	P2D	SOT-223	0.12 g	1000	Tape and reel 7"

4 Revision history

Table 8: Document revision history

Date	Revision	Changes
26-Oct-2017	1	Initial release.

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